



30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
001/	42mΩ @ V _{GS} = -10V	-19.9A
-30V	65mΩ @ V _{GS} = -4.5V	-16A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- General purpose interfacing switches
- Power management functions

Features and Benefits

- Low Rds(ON) Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMP3045LFVWQ)

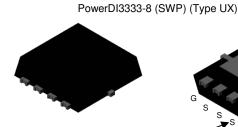
Mechanical Data

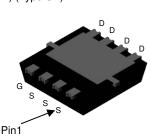
- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208

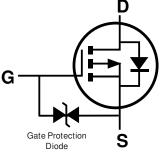
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Top View

Bottom View

Equivalent Circuit

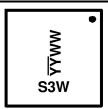
Ordering Information (Note 4)

Part Number	Pookogo	Packing		
Part Number	Package	Qty.	Carrier	
DMP3045LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape & Reel	
DMP3045LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3.000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



S3W = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 22 = 2022)

WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-30	V		
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-5.7 -4.6	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$	ID	-19.9 -15.9	Α
Maximum Continuous Body Diode Forward Current	Is	-1.3	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	-76	Α		
Pulsed Body Diode Forward Current (10µs Pulse, D	lsм	-76	Α		
Avalanche Current (Note 8) L = 1mH	las	-7.8	Α		
Avalanche Energy (Note 8) L = 1mH	Eas	30.8	mJ		

Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	135	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	61	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	5	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BVDSS	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	$V_{DS} = -24V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±10	μA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-2.1	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
Static Drain-Source On-Resistance	D	_	25	42	mΩ	$V_{GS} = -10V$, $I_{D} = -4.9A$
Static Drain-Source On-Nesistance	R _{DS(ON)}	_	43	65	mΩ	$V_{GS} = -4.5V$, $I_{D} = -3.7A$
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	_	782	_	рF	45)/)/ 6)/
Output Capacitance	Coss	_	110	_	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	74	_	рF	1 = 1.0IVID2
Gate Resistance	Rg	_	10.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (VGS = -4.5V)	Qg	_	6.6	_	nC	
Total Gate Charge (VGS = -10V)	Qg	_	13.6	_	nC	V 45V L 40A
Gate-Source Charge	Qgs		2.1	_	nC	$V_{DS} = -15V, I_{D} = -4.9A$
Gate-Drain Charge	Qgd	_	2.7	_	nC	
Turn-On Delay Time	td(ON)	_	4.1	_	ns	
Turn-On Rise Time	tr	_	6.1	_	ns	V _{DD} = -15V, V _{GS} = -10V,
Turn-Off Delay Time	t _{D(OFF)}	_	24.6	_	ns	$I_D = -4.9A, R_G = 6\Omega$
Turn-Off Fall Time	t _F	_	13.1	_	ns]
Reverse Recovery Time	trr	_	12.7	_	ns	1 44 54 -11/-14 4004/
Reverse Recovery Charge	Q _{RR}	_	4.8	_	nC	Is = -11.5A, dl/dt = 100A/µs

Notes:

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.



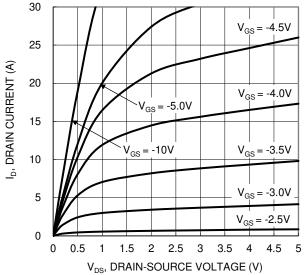


Figure 1. Typical Output Characteristic

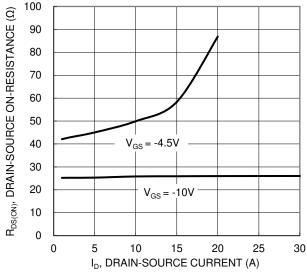


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

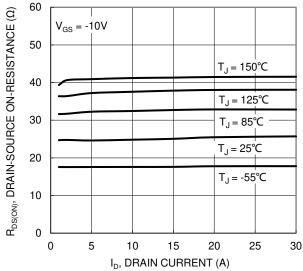


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

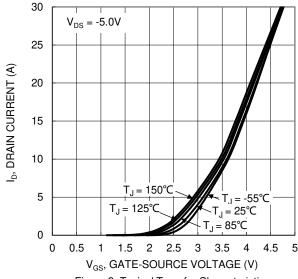


Figure 2. Typical Transfer Characteristic

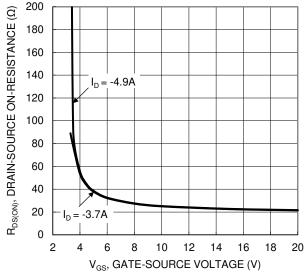


Figure 4. Typical Transfer Characteristic

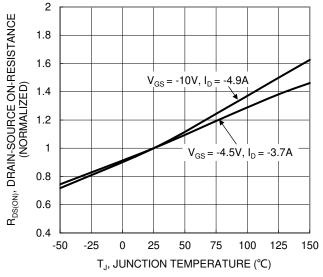


Figure 6. On-Resistance Variation with Temperature



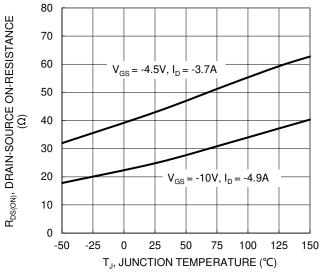


Figure 7. On-Resistance Variation with Temperature

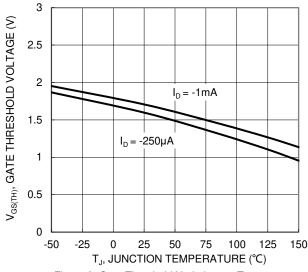


Figure 8. Gate Threshold Variation vs. Temperature

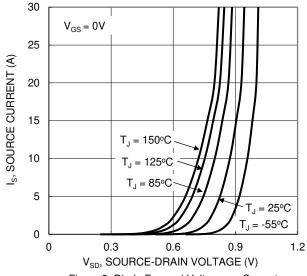


Figure 9. Diode Forward Voltage vs. Current

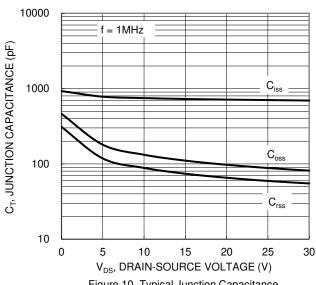
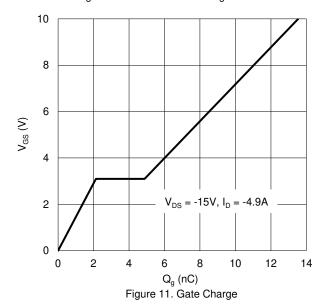


Figure 10. Typical Junction Capacitance



 $R_{DS(ON)}$ ID, DRAIN CURRENT (A) 10 T_C = 25℃ Single Pulse DUT on Infinite DC Heatsink $V_{GS} = -10V$ 0.1 0.1 10 100 V_{DS} , DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area

100



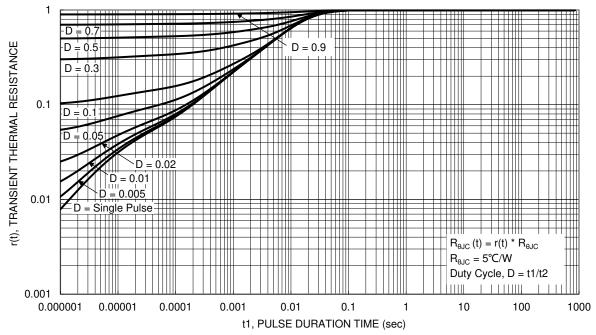


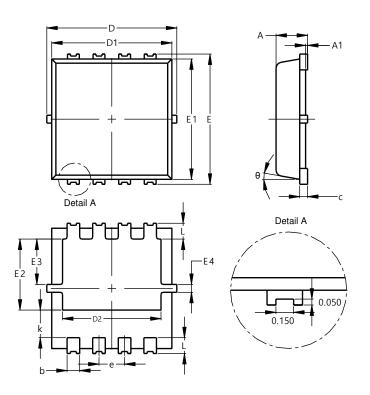
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

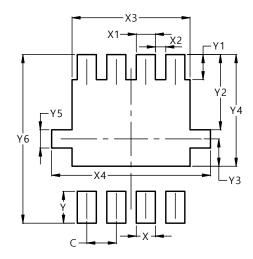


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min Max Ty					
Α	0.75	0.85	0.80			
A 1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	-	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

 $Please \ see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
X	0.420			
X1	0.420			
X2	0.230			
Х3	2.600			
X4	3.500			
Υ	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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